Ck Maiti

List of Publications by Year
in descending order

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284	2,455	23	37
papers	citations	h-index	g-index
		279798	330143

288	288	288	2271
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Deformationâ€induced stress/strain mapping and performance evaluation of aâ€IGZO thinâ€film transistors for flexible electronic applications. Journal of the Society for Information Display, 2021, 29, 130-142.	2.1	3
2	Design study of gate-all-around vertically stacked nanosheet FETs for sub-7nm nodes. SN Applied Sciences, 2021, 3, 1.	2.9	10
3	Investigation of Work Function Variation on the Electrical Performance of sub-7nm GAA FETs. , 2021, , .		3
4	Strained SiGe Channel TFTs For Flexible Electronics Applications. , 2021, , .		0
5	Stress-Engineered AlGaN/GaN High Electron Mobility Transistors Design. , 2021, , .		1
6	Design and simulation of vertically-stacked nanowire transistors at 3 nm technology nodes. Physica Scripta, 2020, 95, 014001.	2.5	11
7	Low Frequency Noise Analysis in Strained-Si Devices. Advances in Intelligent Systems and Computing, 2020, , 409-417.	0.6	0
8	Strain-engineering in nanowire field-effect transistors at 3Ânm technology node. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 118, 113964.	2.7	16
9	Role of stress/strain mapping and random dopant fluctuation in advanced CMOS process technology nodes. International Journal of Nano and Biomaterials, 2020, 9, 18.	0.1	1
10	Vertically-stacked silicon nanosheet field effect transistors at 3 nm technology nodes - simulation at nanoscale. International Journal of Nanoparticles, 2020, 12, 224.	0.3	0
11	Performance Analysis of FinFETs with Strained-Si Fin on Strain-Relaxed Buffer. , 2020, , .		2
12	Performance Analysis of Sub-10nm Vertically Stacked Gate-All-Around FETs. , 2020, , .		1
13	Strain induced variability study in Gate-All-Around vertically-stacked horizontal nanosheet transistors. Physica Scripta, 2020, 95, 065808.	2.5	12
14	Source/Drain Stressor Design for Advanced Devices at 7 nm Technology Node. Nanoscience and Nanotechnology - Asia, 2020, 10, 447-456.	0.7	2
15	Strain engineering in AlGaN/GaN HEMTs for performance enhancement. International Journal of Nano and Biomaterials, 2020, 9, 34.	0.1	0
16	Metal Grain Granularity Induced Variability in Gate-All-Around Si-Nanowire Transistors at 1nm Technology Node. , 2019, , .		4
17	NBTI Degradation and Recovery in Nanowire FETs. , 2019, , .		0
18	High Frequency Performance of AlGaN/GaN HEMTs Fabricated on SiC Substrates. , 2019, , .		0

#	Article	IF	Citations
19	Impacts of NBTI and hot-carrier stress on silicon nanowire transistor characteristics. Nanomaterials and Energy, 2019, 8, 151-158.	0.2	0
20	Fin Shape Dependence of Electrostatics and Variability in FinFETs. Journal of Electronic Materials, 2019, 48, 6742-6752.	2.2	4
21	Performance comparison of strained-SiGe and bulk-Si channel FinFETs at 7â€‰nm technology node. Journal of Micromechanics and Microengineering, 2019, 29, 104001.	2.6	7
22	SPICE Parameter Extraction of Tri-Gate FinFETs-An Integrated Approach. , 2019, , .		1
23	Role of Stress/Strain Mapping in Advanced CMOS Process Technology Nodes. , 2019, , .		3
24	Vertically-Stacked Silicon Nanosheet Field Effect Transistors at 3nm Technology Nodes. , 2019, , .		11
25	Performance and Opportunities of Gate-All-Around Vertically-Stacked Nanowire Transistors at 3nm Technology Nodes. , 2019, , .		5
26	Performance Prediction of Stacked Nanowire Transistors in the Presence of Random Discrete Dopants and Metal Gate Granularity. , 2019, , .		0
27	Stress-Induced Variability Studies in Tri-Gate FinFETs with Source/Drain Stressor at 7Ânm Technology Nodes. Journal of Electronic Materials, 2019, 48, 5348-5362.	2.2	9
28	Performance Evaluation of Gate-All-Around Si Nanowire Transistors with SiGe Strain engineering. , 2019, , .		0
29	Strain Engineering in AlGaN/GaN HEMTs for Performance Enhancement. , 2019, , .		3
30	Electro-thermal assessment of heterojunction tunnel-FET for low-power digital circuits. International Journal of Nanoparticles, 2019, 11, 154.	0.3	1
31	Reliability studies on biaxially tensile strained-Si channel p-MOSFETs. International Journal of Microstructure and Materials Properties, 2019, 14, 28.	0.1	1
32	Study of Strained-Si/SiGe Channel p-MOSFETs Using TCAD. Lecture Notes in Electrical Engineering, 2018, , 181-188.	0.4	0
33	Effects of hot-carrier degradation on the low frequency noise in strained-Si p-MOSFETs. International Journal of Nanoparticles, 2018, 10, 58.	0.3	1
34	Variability Due to Orientation Dependent Oxide Thickness in SOI-FinFETs. , 2018, , .		0
35	Stress Analysis in Uniaxially Strained-SiGe Channel FinFETs at 7N Technology Node. , 2018, , .		0
36	Stress Tuning in NanoScale FinFETs at 7nm. , 2018, , .		2

#	Article	IF	Citations
37	Gate-All-Around Si-Nanowire Transistors: Simulation at Nanoscale. , 2018, , .		2
38	Performance prediction of SOI FinFETs in the presence of random discrete dopants. , 2018, , .		0
39	Image Encryption with a New Fibonacci Transform. , 2018, , .		3
40	Negative bias temperature instability in strained-Si p-MOSFETs. International Journal of Nano and Biomaterials, 2018, 7, 299.	0.1	0
41	Effects of trap position and number dependence of threshold voltage in p-MOSFETs. , 2018, , .		0
42	Assessment of heterojunction SiGe tunnel-FET for low-power digital circuits. , 2017, , .		0
43	Performance enhancement of FinFETs at low temperature. , 2017, , .		1
44	Technology CAD simulations of hot-carrier degradation in strained-Si p-MOSFETs. , 2017, , .		0
45	Simulation of single-event upset in power MOSFETs. , 2017, , .		3
46	A grayscale watermark technique using sub-sampling and singular value decomposition. , 2016, , .		1
47	Beyond silicon: Strained-SiGe channel FinFETs. , 2015, , .		3
48	Noise characterization of Silicon-Germanium HBTs. , 2015, , .		0
49	Switching Mechanism in Au Nanodot-Embedded Nb₂O₅ Memristors. Journal of Nanoscience and Nanotechnology, 2014, 14, 3538-3544.	0.9	6
50	Bipolar resistive switching in different plant and animal proteins. , 2014, , .		1
51	Interface Properties of Atomic Layer Deposited TiO₂/Al₂O₃ Films on In_{0.53}Ga_{0.47}As/InP Substrates. ACS Applied Materials & Interfaces, 2014, 6, 3263-3274.	8.0	24
52	Interlayer thickness dependence of photovoltaic properties of polycrystalline p-Î^2-FeSi2(Al)/n-Si(100) heterojunctions. Journal of Renewable and Sustainable Energy, 2014, 6, 023110.	2.0	6
53	Observation of long term potentiation in papain-based memory devices. , 2014, , .		0
54	Surface Passivation and Interface Properties of Bulk GaAs and Epitaxial-GaAs/Ge Using Atomic Layer Deposited TiAlO Alloy Dielectric. ACS Applied Materials & Interfaces, 2013, 5, 949-957.	8.0	25

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55	Development of remote laboratories using cloud architecture with web instrumentation. , 2013, , .		3
56	Low frequency noise in polycrystalline p-β-FeSi<inf>2</inf>/Ge heterojunction solar cells. , 2013, , .		0
57	Impact of Buffer Layer on Atomic Layer Deposited TiAlO Alloy Dielectric Quality for Epitaxial-GaAs/Ge Device Application. IEEE Transactions on Electron Devices, 2013, 60, 192-199.	3.0	12
58	Graphene oxide-based flexible metalâ€"insulatorâ€"metal capacitors. Semiconductor Science and Technology, 2013, 28, 055002.	2.0	16
59	Enhancing microelectronics education using online semiconductor technology CAD laboratory. , 2013, , .		4
60	Channel thermal noise modeling and high frequency noise parameters of tri-gate FinFETs. , 2013, , .		5
61	Resistive switching in natural silk fibroin protein-based bio-memristors. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1797-1805.	1.8	56
62	Interface Properties of Mixed (TiO₂)_{1â^'x}(Y₂O₃)_xand (Ta₂O₅)_{1â^'x}(Y₂O₃)_x(0â‰¤xâ‰¤1) Gate Dielectrics on Sulfur-Passivated GaAs. Journal of the Electrochemical Society, 2012, 159, H323-H328.	2.9	7
63	Noise characterization of ALD HfO2MOS capacitors with different metal (Au, Pd and Pt) gates. , 2012, , .		0
64	Atomic layer deposited (TiO2)x(Al2O3)1â^'x/In0.53Ga0.47As gate stacks for III-V based metal-oxide-semiconductor field-effect transistor applications. Applied Physics Letters, 2012, 100, 062905.	3.3	30
65	Degradation analysis and characterization of multifilamentary conduction patterns in high-field stressed atomic-layer-deposited TiO2/Al2O3 nanolaminates on GaAs. Journal of Applied Physics, 2012, 112, 064113.	2.5	12
66	Phonon and lattice dynamics in tri-gate FinFETs on (100) and (110) Si substrates. , 2012, , .		1
67	Extending micro and nanoelectronics education through integrated online microelectronics and technology CAD laboratory. , 2012, , .		1
68	Frequency-dependent dielectric response of HfTaO<i>_x</i>-based metalâ€"insulatorâ€"metal capacitors. Semiconductor Science and Technology, 2012, 27, 085002.	2.0	7
69	Flexible metalâ€"insulatorâ€"metal capacitors on polyethylene terephthalate plastic substrates. Semiconductor Science and Technology, 2012, 27, 105001.	2.0	22
70	Effects of constant voltage stressing on HfTaOx/SiGe gate stack. , 2012, , .		0
71	Characterization of traps in SiGe:C channel heterojunction PMOSFETs. Proceedings of SPIE, 2012, , .	0.8	0
72	Effects of substrate strain and electrical stress on lattice dynamics, defects, and traps in strained-Si/Si0.81Ge0.19â€‰n-type metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2012, 111, 104507.	2.5	2

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73	Bipolar Resistive Switching in Al/HfO₂/In_{0.53}Ga_{0.47}As MIS Structures. ECS Journal of Solid State Science and Technology, 2012, 1, N149-N152.	1.8	10
74	Electrical properties and noise characterization of HfO2 gate dielectrics on strained SiGe layers. Thin Solid Films, 2012, 522, 267-273.	1.8	3
75	Common interface platform for development of remote laboratories. , 2012, , .		2
76	Electrical and charge trapping properties of HfO<inf>2</inf>/Al<inf>2</inf>O<inf>3</inf> bilayer gate dielectrics on In<inf>0.53</inf>Ga<inf>0.47</inf>As substrates. , 2012, , .		0
77	Low frequency noise in iron disilicide hetero-junction solar cells. , 2012, , .		2
78	RF Laboratory for Engineering Education. , 2012, , .		3
79	Studies on Lattice vibration, impurity and defects in MIS structures using Hf-based dielectrics on Si and SiGe substrates. , 2012, , .		0
80	Remote operation of optical microscopes for use in science and engineering laboratories. , 2012, , .		0
81	Study of the spatial distribution of breakdown spots in MOS devices in case of important edge effect anomalies. , 2012, , .		1
82	Studies on switching mechanisms in Pd-nanodot embedded Nb2O5 memristors using scanning tunneling microscopy. Thin Solid Films, 2012, 520, 6648-6652.	1.8	23
83	Hybrid orientation technology and strain engineering for ultra-high speed MOSFETs. Bulletin of Materials Science, 2012, 35, 859-865.	1.7	3
84	Polycrystalline p-β-FeSi<inf>2</inf>(Al) on n-Si(100): Heterojunction thin-film solar cells. , 2012, , .		2
85	A binary watermarking scheme using quantization levels of BTC-PF method. , 2012, , .		0
86	A Natural Silk Fibroin Proteinâ€Based Transparent Bioâ€Memristor. Advanced Functional Materials, 2012, 22, 4493-4499.	14.9	202
87	LabVIEW controlled atomic force microscopy for remote nanoelectronics laboratory. , 2012, , .		2
88	Degradation and breakdown characteristics of Al/HfYOx/GaAs capacitors. Thin Solid Films, 2012, 520, 2956-2959.	1.8	1
89	Characterization of epitaxial GaAs MOS capacitors using atomic layer-deposited TiO2/Al2O3 gate stack: study of Ge auto-doping and p-type Zn doping. Nanoscale Research Letters, 2012, 7, 99.	5.7	13
90	Direct Nanoscale Observation of Resistance Switching with Au Nano-Dots Embedded Nb₂O₅ by Scanning Tunneling Microscopy. Nanoscience and Nanotechnology Letters, 2012, 4, 394-399.	0.4	8

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91	Role of online laboratory in nanoelectronics education. , 2011, , .		0
92	Design and Development of a Cost-Effective Online Electronic Circuits Laboratory. , 2011, , .		4
93	Impact of Top (Pt, Au, and Al) Electrodes on HfAlO[sub x]-Based MIM Capacitors. Journal of the Electrochemical Society, 2011, 158, H44.	2.9	10
94	Power-law logistic model for the current-time characteristic of metal gate/high-K/III-V semiconductor capacitors. , 2011, , .		1
95	Online technology CAD laboratory for microelectronics education. , 2011, , .		7
96	Electrical Properties of SiGe MOS Capacitors with Ultrathin ALD Hafnium Dioxide. ECS Transactions, 2011, 35, 513-520.	0.5	1
97	Effects of Ti incorporation on the interface properties and band alignment of HfTaOx thin films on sulfur passivated GaAs. Applied Physics Letters, 2011, 98, 022901.	3.3	19
98	Si1â^’xGex metal-oxide-semiconductor capacitors with HfTaOx gate dielectrics. Thin Solid Films, 2011, 520, 101-105.	1.8	7
99	An extension of the Curie-von Schweidler law for the leakage current decay in MIS structures including progressive breakdown. Microelectronics Reliability, 2011, 51, 1535-1539.	1.7	12
100	Model for the leakage current decay in high-field stressed Al/HfYOx/GaAs structures. Microelectronic Engineering, 2011, 88, 1295-1297.	2.4	1
101	Temperature dependence of TaAlOx metal-insulator-metal capacitors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AC06.	1.2	1
102	Interfacial and Electrical Properties of GaAs Metal-Oxide-Semiconductor Device with TiOxNy High-k Gate Dielectrics. ECS Transactions, 2011, 35, 325-332.	0.5	3
103	Flatband Voltage Characteristics of Hf-Incorporated Y[sub 2]O[sub 3]/Strained-Si Gate Stacks with Au, Pt, and Ni Metal Gates. Electrochemical and Solid-State Letters, 2011, 14, H80.	2.2	4
104	Interface Structure and Charge Trapping in Hf-Incorporated Y2O3 Gate Dielectrics on Germanium. ECS Transactions, 2011, 35, 835-845.	0.5	0
105	Sputter-Deposited La2O3on p-GaAs for Gate Dielectric Applications. Journal of the Electrochemical Society, 2011, 159, G15-G22.	2.9	28
106	Surface Passivation of GaAs Substrates with SiO2 Deposited Using ALD. Electrochemical and Solid-State Letters, 2011, 14, G52.	2.2	10
107	Chemical Bonding States of Plasma Nitrided High-k/Ge Gate Stack. Electrochemical and Solid-State Letters, 2011, 14, H167.	2.2	3
108	Structural and Electrical Properties of Radio Frequency Sputtered HfTaO_x Films for High-k Gate Insulator. Japanese Journal of Applied Physics, 2011, 50, 101101.	1.5	3

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109	Negative bias temperature instability in strain-engineered p-MOSFETs: a simulation study. Journal of Computational Electronics, 2010, 9, 1-7.	2.5	6
110	HfAlO high-k gate dielectric on SiGe: Interfacial reaction, energy-band alignment, and charge trapping properties. Microelectronic Engineering, 2010, 87, 2234-2240.	2.4	18
111	Preparation and characterization of TaAlOx high-Îº dielectric for metalâ€“insulatorâ€“metal capacitor applications. Thin Solid Films, 2010, 519, 423-429.	1.8	12
112	Characterization of Y2O3 gate dielectric on n-GaAs substrates. Applied Surface Science, 2010, 256, 2245-2251.	6.1	40
113	Random Telegraph Noise characterization of p-type silicon nanowire FinFETs. , 2010, , .		2
114	NONEQUILIBRIUM GREEN'S FUNCTION BASED QUANTUM TRANSPORT SIMULATION FOR STRAINED-ENGINEERED NANOSCALE TRANSISTORS IN THE PRESENCE OF ELECTRONâ€“PHONON INTERACTIONS. International Journal of Nanoscience, 2010, 09, 327-333.	0.7	0
115	Thermal stability of HfOxNygate dielectrics on p-GaAs substrates. Semiconductor Science and Technology, 2010, 25, 125009.	2.0	4
116	Degradation behavior of TaYO<inf>x</inf>-based metal-insulator-metal capacitors. , 2010, , .		0
117	Reliability and breakdown characteristics of HfO<inf>2</inf>-based GaAs metal-oxide-semiconductor capacitors with a thin Si interface layer. , 2010, , .		0
118	Charge trapping characteristics of HfYO<inf>x</inf> gate dielectrics on SiGe. , 2010, , .		0
119	Cost-effectiveweb-based electronics laboratory using NI MultiSim, LabVIEW and ELVIS II. , 2010, , .		7
120	Design and optimization of c-Silicon solar cell using Process Compact Model (PCM). , 2009, , .		0
121	Effect of channel implantation on the design of high frequency nanoscale n-FinFETs. , 2009, , .		1
122	Charge-based Mobility Modeling for Organic Semiconductors. , 2009, , .		0
123	Characterization of RF sputter deposited HfAlOx dielectrics for MIM capacitor applications. , 2009, , .		0
124	Charge trapping property of RTN grown oxynitride films on strained-Si. , 2009, , .		0
125	Charge Trapping Characteristics of TaYOx Gate Dielectrics on Ge under DC and AC Stressing. ECS Transactions, 2009, 19, 699-710.	0.5	1
126	Reliability behavior of TaAlOx Metal-Insulator-Metal capacitors. , 2009, , .		1

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127	Modeling of radiation-induced displacement damage in silicon solar cells: Frenkel defect. , 2009, , .		0
128	Charge Trapping in HfYOx Gate Dielectrics on Strained-Si. ECS Transactions, 2009, 25, 163-168.	0.5	1
129	Reliability and charge trapping properties of ZrO<inf>2</inf> gate dielectric on Si passivated p-GaAs. , 2009, , .		0
130	Paramagnetic defects and charge trapping behavior of ZrO₂films deposited on germanium by plasma-enhanced CVD. Semiconductor Science and Technology, 2009, 24, 025026.	2.0	3
131	Effects of an ultrathin Si passivation layer on the interfacial properties of RF-sputtered HfYOxon n-GaAs substrates. Semiconductor Science and Technology, 2009, 24, 085026.	2.0	5
132	Charge trapping and reliability characteristics of sputtered Y₂O₃high-<i>k</i>dielectrics on N- and S-passivated germanium. Semiconductor Science and Technology, 2009, 24, 085006.	2.0	13
133	Reliability of Ti-based Gate Dielectrics on strained-Si0.91Ge0.09 and Ge under Dynamic and AC Stressing. ECS Transactions, 2009, 16, 223-227.	0.5	0
134	Performance improvement of flash memory using AlN as charge-trapping Layer. Microelectronic Engineering, 2009, 86, 299-302.	2.4	28
135	High performance TaYOx-based MIM capacitors. Microelectronic Engineering, 2009, 86, 2180-2186.	2.4	12
136	High Density MIM Capacitors Using HfAlO_x. ECS Transactions, 2009, 25, 201-207.	0.5	4
137	Effects of Rapid Thermal Annealing Temperature on Performances of Nanoscale FinFETs. Journal of Semiconductor Technology and Science, 2009, 9, 266-272.	0.4	4
138	Reliability of ultra-thin titanium dioxide (TiO2) films on strained-Si. Thin Solid Films, 2008, 517, 27-30.	1.8	10
139	CMOS performance enhancement in Hybrid Orientation Technologies. Journal of Computational Electronics, 2008, 7, 181-186.	2.5	3
140	Studies on dielectric relaxation and defect generation for reliability assessments in ultrathin high-k gate dielectrics on Ge. Microelectronic Engineering, 2008, 85, 2207-2212.	2.4	6
141	Charge trapping characteristics in high-k gate dielectrics on germanium. Thin Solid Films, 2008, 517, 163-166.	1.8	9
142	Internal photoemission study on charge trapping behavior in rapid thermal oxides on strained-Si/SiGe heterolayers. Applied Surface Science, 2008, 255, 2971-2977.	6.1	6
143	Reliability assessment of SiO2/ZrO2 stack gate dielectric on strained-Si/Si0.8Ge0.2 heterolayers under dynamic and AC stress. Materials Science in Semiconductor Processing, 2008, 11, 254-258.	4.0	1
144	Reliability of ultra thin ZrO2 films on strained-Si. Microelectronics Reliability, 2008, 48, 682-692.	1.7	12

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145	Reliability of ZrO<inf>2</inf>/GeO<inf>x</inf>N<inf>y</inf> stacked high-k dielectrics on Ge under dynamic and pulsed voltage stress. , 2008, , .		0
146	Hot carrier degradation in nanowire (NW) FinFETs. , 2008, , .		3
147	Strained-Si MOSFETs for Low-Power Applications. ECS Transactions, 2008, 14, 203-211.	0.5	0
148	DIBL in short-channel strained-Si n-MOSFET. , 2008, , .		6
149	Stress-induced degradation in strain-engineered nMOSFETs. , 2008, , .		1
150	TiO2/GeOxNystacked gate dielectrics for Ge-MOSFETs. Semiconductor Science and Technology, 2007, 22, 1352-1361.	2.0	29
151	Scaling of Strain-Engineered MOSFETs. IETE Journal of Research, 2007, 53, 263-276.	2.6	1
152	Charge trapping properties of ultra-thin TiO2films on strained-Si. Semiconductor Science and Technology, 2007, 22, 774-783.	2.0	9
153	Nitrogen engineering in Titanium based high-k gate dielectrics on Ge. , 2007, , .		0
154	Low temperature behavior of strained-Si n-MOSFETs. , 2007, , .		0
155	Determination of minority carrier lifetime and interface trap density in Ge MIS capacitors. , 2007, , .		0
156	Ultrathin High-k Gate Dielectric Films on Strained-Si/SiGe Heterolayers. IETE Journal of Research, 2007, 53, 237-251.	2.6	0
157	Finite element analysis of heat transfer in nanowires (NWs). , 2007, , .		0
158	Reliability predictions for strained-Si/SiGe Quantum-well p-MOSFETs. , 2007, , .		0
159	RF performance of process-induced strain-engineered n-MOSFETs. , 2007, , .		0
160	Technology CAD of non-volatile SONOS memory devices. , 2007, , .		0
161	Magnetic resonance and internal photoemission study of trap centers in high-k dielectric films on Ge. , 2007, , .		1
162	Internal Photoemission Study on Reliability of Ultra-thin Zirconium Oxide Films on Strained-Si. , 2007, , .		3

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163	Strained-Si heterostructure field effect devices: Strain-engineering in CMOS technology. , 2007, , .		2
164	Radiation effects on strain-engineered p-MOSFETs. , 2007, , .		1
165	Design of active inductors in SiGe/SiGe:C processes for RF applications. International Journal of RF and Microwave Computer-Aided Engineering, 2007, 17, 455-468.	1.2	0
166	Structural and optical properties of ZnO films grown on silicon and their applications in MOS devices in conjunction with ZrO2 as a gate dielectric. Bulletin of Materials Science, 2007, 30, 247-254.	1.7	35
167	Efficient Multi-method Rule Learning for Pattern Classification Machine Learning and Data Mining. , 2007, , 324-331.		0
168	Rapid thermal oxidation of Ge-rich Si1â^'xGex heterolayers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 84-90.	2.1	11
169	Reliability of Ultra-thin Zirconium Dioxide (ZrO2) Films on Strained-Si. , 2006, , .		1
170	Simulation Study of Hot-electron Reliability in strained-Si n-MOSFETs. , 2006, , .		0
171	Prediction of barrier inhomogeneities and carrier transport in Ni-silicided Schottky diode. Applied Surface Science, 2006, 252, 3933-3937.	6.1	4
172	Modeling of low temperature SiGe oxidation. Materials Science in Semiconductor Processing, 2006, 9, 668-672.	4.0	0
173	Electrical properties of SiO2/TiO2 high-k gate dielectric stack. Materials Science in Semiconductor Processing, 2006, 9, 909-917.	4.0	31
174	Physico-chemical and electrical properties of rapid thermal oxides on Ge-rich SiGe heterolayers. Applied Surface Science, 2006, 253, 1323-1329.	6.1	6
175	Technology CAD for germanium CMOS circuit. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 261-266.	3.5	1
176	Implementation of a scalable VBIC model for SiGe:C HBTs. Solid-State Electronics, 2006, 50, 399-407.	1.4	2
177	Determination of the interface properties of Ni-silicided strained-Si/SiGe heterostructure Schottky diodes using capacitanceâ€"voltage technique. Solid-State Electronics, 2006, 50, 1269-1275.	1.4	13
178	Determination of the valence band offset and minority carrier lifetime in Ge-rich layers on relaxed-SiGe. Thin Solid Films, 2006, 504, 73-76.	1.8	6
179	Effect of silicidation on the electrical characteristics of polycrystalline-SiGe Schottky diode. Thin Solid Films, 2006, 504, 86-90.	1.8	2
180	High frequency characterization and continuum modeling of ultrathin high-k (ZrO2) gate dielectrics on strained-Si. Thin Solid Films, 2006, 504, 183-187.	1.8	31

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181	Surface roughness and interface engineering for gate dielectrics on strained layers. Journal of Materials Science: Materials in Electronics, 2006, 17, 711-722.	2.2	3
182	Interface Properties of Room-Temperature-Grown Oxides on Si[sub 0.15]Ge[sub 0.85] Layers. Journal of the Electrochemical Society, 2006, 153, G511.	2.9	1
183	Dielectric Relaxation and Defect Generation Under Pulsed and Constant Voltage Stressing of Ultrathin TiO2 Films on Strained-Si/Si0.8Ge0.2. ECS Transactions, 2006, 3, 1229-1240.	0.5	0
184	Analysis of interface states of Al/TiO2/Si0.3Ge0.7MIS structures using the conductance technique. Semiconductor Science and Technology, 2006, 21, 335-340.	2.0	20
185	Leakage current characteristics and the energy band diagram of Al/ZrO2/Si0.3Ge0.7hetero-MIS structures. Semiconductor Science and Technology, 2006, 21, 467-472.	2.0	36
186	Modeling of Lossy MOS Capacitors on Ge-Rich Si0.15Ge0.85 Substrates. ECS Transactions, 2006, 3, 291-297.	0.5	0
187	Quantum-mechanical modeling of current-voltage characteristics of Ti-silicided Schottky diodes. Journal of Applied Physics, 2006, 99, 113707.	2.5	2
188	Effects of annealing on the electrical properties of TiO2 films deposited on Ge-rich SiGe substrates. Journal of Applied Physics, 2006, 100, 023706.	2.5	10
189	Current conduction mechanism in TiO2 gate dielectrics. Microelectronic Engineering, 2005, 81, 188-193.	2.4	61
190	Technology CAD of silicided Schottky barrier MOSFET for elevated sourceâ€“drain engineering. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 124-125, 424-430.	3.5	2
191	Effect of annealing on interface state density of Ni-silicided/Si1â^'xGex Schottky diode. Materials Science in Semiconductor Processing, 2005, 8, 249-253.	4.0	14
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